

TB0640H thru TB4000H

SURFACE MOUNT THYRISTOR SURGE PROTECTIVE DEVICE

Bi-Directional

VDRM - **58 to 360** Volts IPP - **100** Amperes

SMB

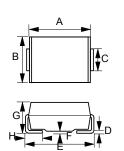
FEATURES

- Oxide Glass Passivated Junction
- Bidirectional protection in a single device
- Surge capabilities up to 100A @ 10/1000us or 400 @ 8/20us
- High off state Impedance and low on state voltage
- Plastic material has UL flammability classification 94V-0

MECHANICAL DATA

• Case : Molded plastic

Polarity: Denotes none cathode bandWeight: 0.003 ounces, 0.093 grams



SMB					
DIM.	MIN.	MAX.			
Α	4.06	4.57			
В	3.30	3.94			
С	1.96	2.21			
D	0.15	0.31			
Е	5.21	5.59			
F	0.05	0.20			
G	2.01	2.62			
Н	0.76	1.52			
All Dimensions in millimeter					

MAXIMUM RATINGS

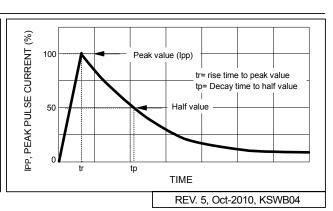
CHARACTERISTICS	SYMBOL	VALUE	UNIT
Non-repetitive peak impulse current @ 10/1000us	IPP	100	Α
Non-repetitive peak On-state current @ 8.3ms (one half cycle)	ITSM	50	Α
Junction temperature range	TJ	-40 to +150	°C
storage temperature range	TSTG	-55 to +150	°C

THERMAL RESISTANCE

CHARACTERISTICS	SYMBOL	VALUE	UNIT
Junction to leads	Rth(J-L)	20	°C/W
Junction to ambient on print circuit (on recommended pad layout)	Rth(J-A)	100	°C/W
Typical positive temperature coefficient for brekdown voltage	△VBR/△TJ	0.1	%/℃

MAXIMUM RATED SURGE WAVEFORM

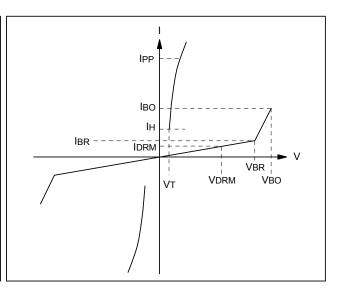
WAVEFORM	STANDARD	IPP (A)
2/10 us	GR-1089-CORE	500
8/20 us	IEC 61000-4-5	400
10/160 us	FCC Part 68	250
10/560 us	FCC Part 68	200
10/700 us	ITU-T K20/K21	160
10/1000 us	GR-1089-CORE	100





PARAMETER	RATED REPETITIVE OFF-STATE VOLTAGE	OFF-STATE LEAKAGE CURRENT @ VDRM	BREAKOVER VOLTAGE	ON-STATE VOLTAGE @ IT=1.0A		KOVER RENT		DING RENT	OFF-STATE CAPACITANCE
SYMBOL	VDRM	IDRM	VBO	VT	IBO		lH		Со
UNITS	Volts	uA	Volts	Volts	mA		mA		pF
LIMIT	Max	Max	Max	Max	Min	Max	Min	Max	Тур
TB0640H	58	5	77	3.5	50	800	150	800	200
TB0720H	65	5	88	3.5	50	800	150	800	200
ТВ0900Н	75	5	98	3.5	50	800	150	800	200
TB1100H	90	5	130	3.5	50	800	150	800	120
TB1300H	120	5	160	3.5	50	800	150	800	120
TB1500H	140	5	180	3.5	50	800	150	800	120
TB1800H	170	5	220	3.5	50	800	150	800	120
TB2300H	190	5	265	3.5	50	800	150	800	80
TB2600H	220	5	300	3.5	50	800	150	800	80
TB3100H	275	5	350	3.5	50	800	150	800	80
TB3500H	320	5	400	3.5	50	800	150	800	80
TB4000H	360	5	450	3.5	50	800	150	800	80

SYMBOL	PARAMETER		
VDRM	Stand-off Voltage		
IDRM	Leakage current at stand-off voltage		
VBR	Breakdown voltage		
IBR	Breakdown current		
VBO	Breakover voltage		
IBO	Breakover current		
lн	Holding current	Note: 1	
VT	On state voltage		
IPP	Peak pulse current		
Co	Off state capacitance	Note: 2	

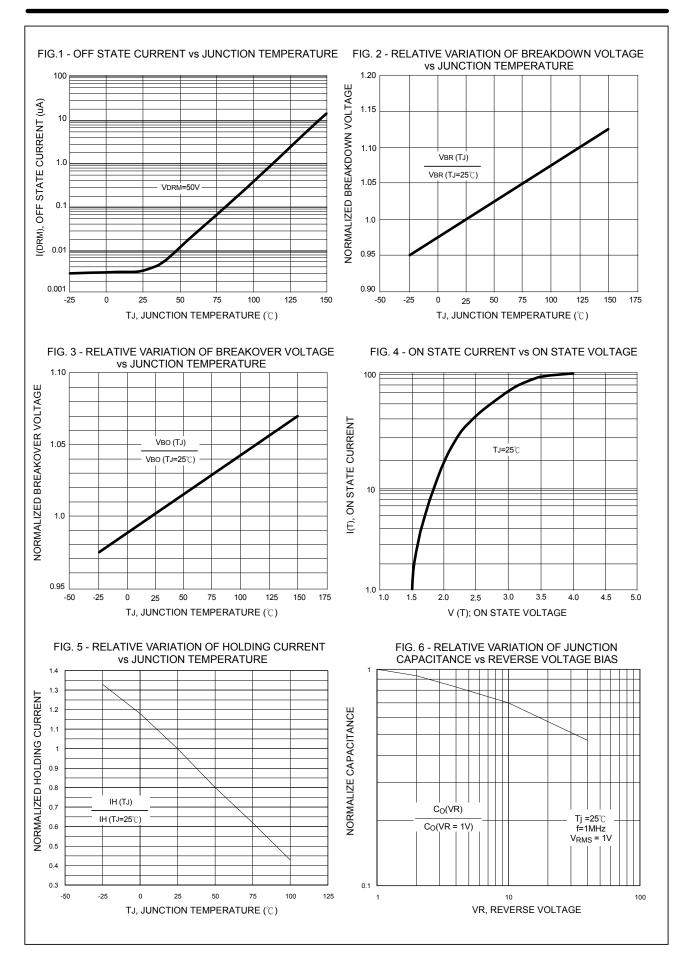


NOTES: 1. IH > (VL/RL) If this criterion is not obeyed, the TSPD Triggers but does not return correctly to high-resistance state.

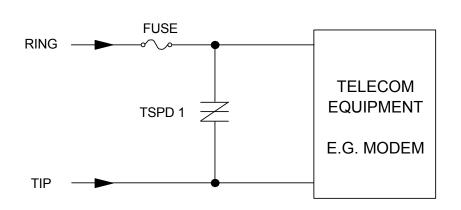
The Surge recovery time does not exceed 30ms.

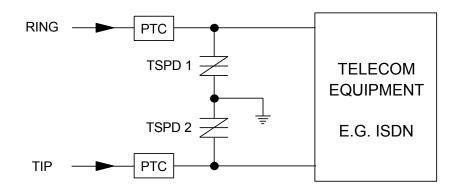
2. Off-state capacitance measured at f=1.0MHz; 1.0VRMS signal; VR=2VDC bias.

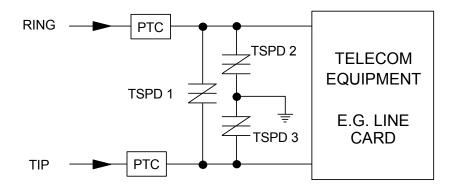












The PTC (Positive Temperature Coefficient) is an overcurrent protection device



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